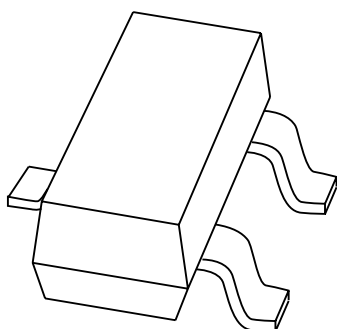


# DATA SHEET



**PBSS4130T**

30 V, 1 A

NPN low  $V_{CEsat}$  (BISS) transistor

Product specification

2003 Nov 27

# 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

PBSS4130T

## FEATURES

- Low collector-emitter saturation voltage  $V_{CEsat}$
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

## APPLICATIONS

- Power management
  - DC/DC conversion
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral driver
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load drivers (e.g. relays, buzzers and motors).

## DESCRIPTION

NPN BISS transistor in a SOT23 plastic package providing ultra low  $V_{CEsat}$  and  $R_{CEsat}$  parameters.  
PNP complement: PBSS5130T.

## MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS4130T	*3C

## Note

- \* = p: made in Hong Kong.  
\* = t: made in Malaysia.  
\* = W: made in China.

## ORDERING INFORMATION

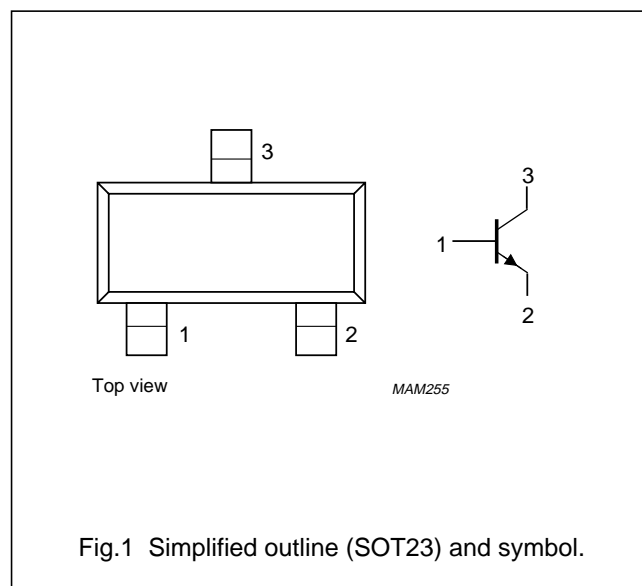
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS4130T	–	plastic surface mounted package; 3 leads	SOT23

## QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
$V_{CEO}$	collector-emitter voltage	30	V
$I_C$	collector current (DC)	1	A
$I_{CM}$	peak collector current	3	A
$R_{CEsat}$	equivalent on-resistance	220	mΩ

## PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



# 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

PBSS4130T

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	40	V
$V_{CEO}$	collector-emitter voltage	open base	–	30	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	1	A
$I_{CM}$	peak collector current		–	3	A
$I_{BM}$	peak base current		–	300	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	300	mW
		$T_{amb} \leq 25\text{ °C}$ ; note 2	–	480	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

## Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

## Notes

1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

# 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

PBSS4130T

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 30\text{ V}; I_E = 0; T_J = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 4\text{ V}; I_C = 0$	–	–	100	nA
$h_{FE}$	DC current gain	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}$	350	470	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}$	300	450	–	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	300	420	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	–	90	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	–	120	mV
		$I_C = 750\text{ mA}; I_B = 15\text{ mA}$	–	–	220	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{note 1}$	–	–	270	mV
$R_{CEsat}$	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	240	$\text{m}\Omega$
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}; \text{note 1}$	–	–	1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}$	–	–	0.75	V
$f_T$	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0; f = 1\text{ MHz}$	–	–	20	pF

### Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

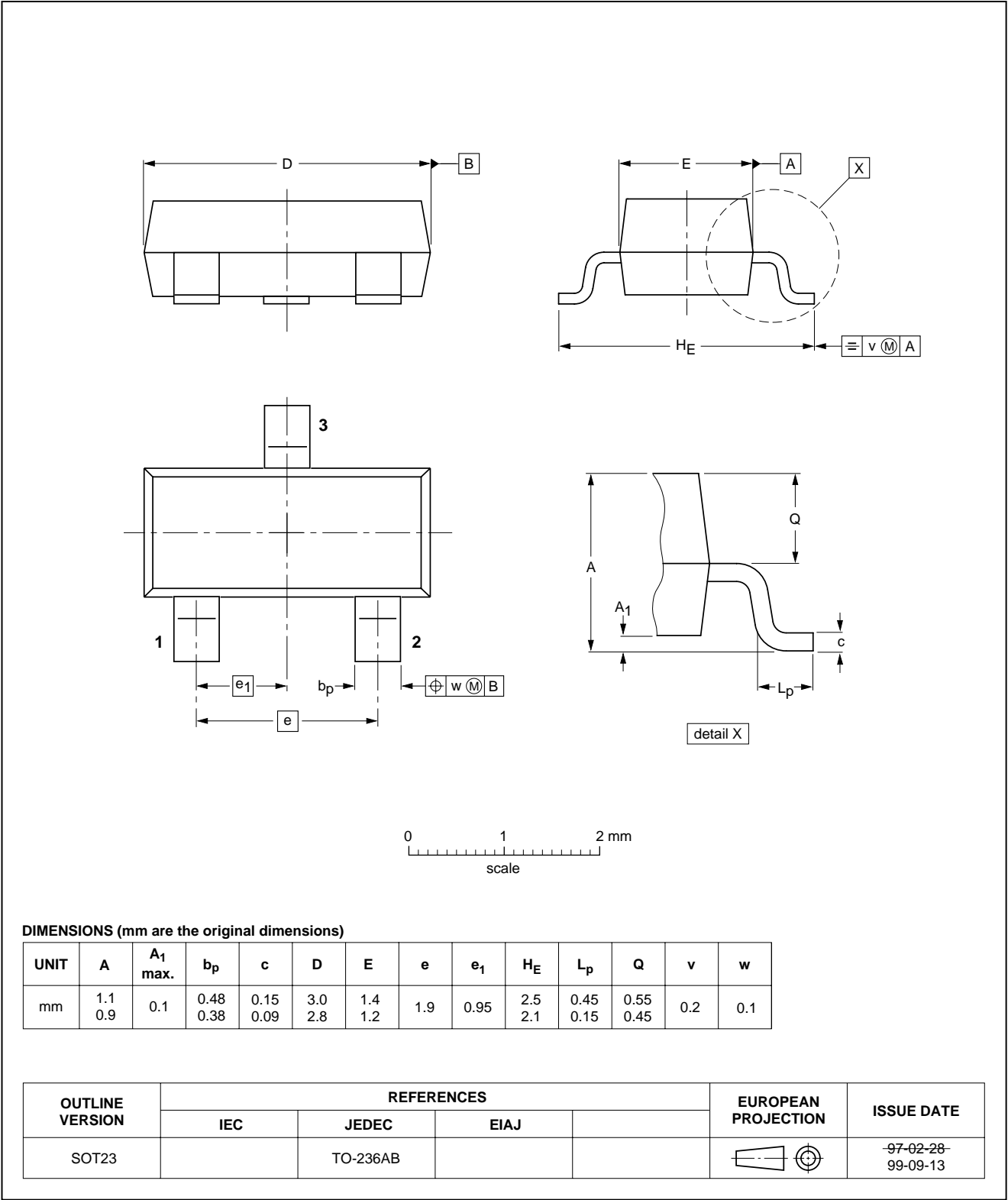
30 V, 1 A  
NPN low  $V_{CEsat}$  (BISS) transistor

PBSS4130T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



# 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

PBSS4130T

## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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## **Contact information**

For additional information please visit **<http://www.semiconductors.philips.com>**. Fax: **+31 40 27 24825**

For sales offices addresses send e-mail to: **[sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com)**.

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